

S8050 S8050A M8050 MMT8050 SS8050 A6802

#### SOT-23

- 1. BASE
- 2. EMITTER
- 3. COLLECTOR



#### ■FEATURES 特點

Low Frequency Power Amplifier 低頻功率放大 Suitable for Driver Stage of Small Motor 小馬達驅動 Complementary to 8550 与 8550互补

## ■最大額定値(T<sub>a</sub>=25℃)

CHARACTERISTIC 特性參數	Symbol 符號	Rating 額定値	Unit 單位
Collector-Base Voltage 集電極-基極電壓	$V_{CBO}$	40 25(C6802)	Vdc
Collect-Emitter Voltage 集電極-發射極電壓	$V_{CEO}$	25 18(C6802)	Vdc
Emitter-Base Voltage 發射極-基極電壓	$V_{\mathrm{EBO}}$	5.0	Vdc
Collector Current 集電極電流	Ic	500(\$8050A,\$8050) 1000(M8050) 1200(MMT8050) 1500(\$\$8050) 1800(\$\$6802)	mAdc
Collector Power Dissipation 集電極耗散功率	$P_{\rm C}$	225	mW
Junction Temperature 結溫	T <sub>i</sub>	150	°C
Storage Temperature Range 儲存溫度	$T_{\rm stg}$	-55∼150	$^{\circ}\! \mathbb{C}$

#### ■DEVICE MARKING 打標

**S8050A=J3Y. S8050=J3Y M8050=Y1. MMT8050=Y1 SS8050=Y.1 C**6802=6802

## ■H<sub>FE</sub> RANGE 放大倍數分檔

H<sub>FE</sub> (85~150), (120~220) (200~300), (280~400)



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# ■ELECTRICAL CHARACTERISTICS 電特性

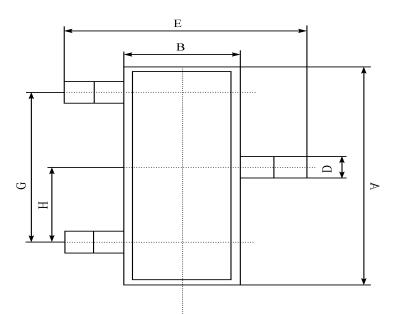
( $T_A$ =25℃ unless otherwise noted 如無特殊說明,溫度爲 25℃)

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Characterstic 特性參數	Symbol 符號	Test Condition 測試條件	Min. 最小値	Typ. 典型値	Max. 最大値	Unit 單位
Collector Cutoff Current 集電極截止電流	$I_{CBO}$	$V_{CB} = 30V, I_{E} = 0$	_	_	0.1	μΑ
Emitter Cutoff Current 發射極截止電流	$I_{EBO}$	$V_{EB}=5V,I_{C}=0$	_	_	0.1	μΑ
Collector-Base Breakdown Voltage 集電極-基極擊穿電壓	V <sub>(BR)CBO</sub>	I <sub>C</sub> =100 μ A (C6802)	40 (25)		_	V
Collector-Emitter Breakdown Voltage 集電極-發射極擊穿電壓	V <sub>(BR)CEO</sub>	I <sub>C</sub> =10mA (C6802)	25 (18)			V
Emitter-Base Breakdown Voltage 發射極-基極擊穿電壓	V <sub>(BR)EBO</sub>	$I_{E}$ =100 $\mu$ A	5		_	V
DC Current Gain 直流電流增益	$H_{FE}(1)$	$V_{CE}=1V,I_{C}=100mA$	85		400	
	H <sub>FE</sub> (2)	$V_{\text{CE}}\!\!=\!\!1V,\\ I_{\text{C}}\!\!=\!\!1800\text{mA}(\text{C6802})\\ I_{\text{C}}\!\!=\!\!800\text{mA}\\ \text{(M8050,MMT8050, SS8050)}\\ I_{\text{C}}\!\!=\!\!500\text{mA}(\text{S8050})\\ I_{\text{C}}\!\!=\!\!500\text{mA}(\text{S8050A})$	50 40 40 30	_	_	_
Collector-Emitter Saturation Voltage 集電極-發射極飽和壓降	V <sub>CE(sat)</sub>	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA	_		0.6	V
Base-Emitter Voltage 基極-發射極電壓	$ m V_{BE}$	V <sub>CE</sub> =1V,I <sub>C</sub> =10mA	_	0.8	1.0	V
Transition Frequency 特徴頻率	$f_T$	V <sub>CE</sub> =5V,I <sub>C</sub> =10mA	100	120		MHz
Collector Output Capacitance 輸出電容	$C_{ob}$	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$	_	13	30	pF

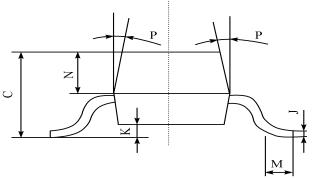


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### ■DIMENSION 外形封裝尺寸



序號	數值及公差
A	$2.90 \pm 0.10$
В	$1.30 \pm 0.10$
С	$1.00 \pm 0.10$
D	$0.40 \pm 0.10$
Е	$2.40 \pm 0.20$
G	$1.90 \pm 0.10$
Н	$0.95 \pm 0.05$
J	$0.13 \pm 0.05$
K	0.00-0.10
M	≥0.2
N	$0.60 \pm 0.10$
P	$7\pm2\degree$



This datasheet presents technical data of Tak Cheong's Silicon Rectifier Diodes. Complete specifications for the individual devices are provided in the form of datasheets. A comprehensive Selector Guide is included to simplify the task of choosing the best set of components required for a specific application. For additional information, please visit our website <a href="http://www.takcheong.com">http://www.takcheong.com</a>.

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